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Color Code:

Red – Plasma Etching

Blue – Advanced Devices

For full patent text, please use patent number search feature at United States Patent and Trademark Office:

<http://patft.uspto.gov/netahtml/srchnum.htm>

US Patent Nr.	Title	Assignee	Filed	Date of Patent
6,602,434	Process for etching oxide using hexafluorobutadiene or related fluorocarbons and manifesting a wide process window	Applied Materials Inc.	11/15/99	8/5/03
6,605,487	Method for the manufacture of micro-mechanical components	Infineon Technologies Aktiengesellschaft	12/20/01	8/12/03
6,605,498	Semiconductor transistor having a backfilled channel material	Intel Corporation	3/29/02	8/12/03
6,605,543	Process to control etch profiles in dual-implanted silicon films	Koninklijke Philips Electronics N.V.	12/30/99	8/12/03
6,605,843	Fully depleted SOI device with tungsten damascene contacts and method of forming same	Advanced Micro Device, Inc.	8/11/00	8/12/03
6,605,847	Semiconductor device having gate all around type transistor and method of forming the same	Samsung Electronics Co.	1/3/02	8/12/03

6,606,738	Analytical model for predicting the operating process window for lithographic patterning techniques based on photoresist trim technology	Advanced Micro Device, Inc.	3/30/01	8/12/03
6,607,675	Method of etching carbon-containing silicon oxide films	Applied Materials Inc.	8/29/00	8/19/03
6,607,950	MIS transistors with a metal gate and high-k dielectric and method of forming	Interuniversitair Microelektronic Centrum (IMEC)	3/30/01	8/19/03
6,607,985	Gate stack and etch process	Texas Instruments	1/28/98	8/19/03
6,611,023	Field effect transistor with self aligned double gate and method of forming same	Advanced Micro Device, Inc.	5/1/01	8/26/03
6,611,032	Methods for forming wordlines, transistor gates, and conductive interconnects, and wordline, transistor gate, and conductive interconnect structures	Micron Technology, Inc.	6/11/01	8/26/03